

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings of the claims in the application:

Listing of Claims:

1. (Withdrawn and currently amended) A stent comprising a compound including Ti, N, C;
~~or including Ti, N, O, or both,~~ implanted on a molecular or atomic level at a depth within
at least a region of a surface of the stent and a layer of TiN_xC_y disposed over the
compound.
2. (Previously Presented) The stent of Claim 21, wherein x is 1 and y is 1 or 2.
3. (Previously Presented) The stent of Claim 21, wherein the depth of an implanted TiN_xO_y
compound is not greater than about 2000 Å from the surface of the stent.
4. (Previously Presented) The stent of Claim 21, wherein the layer of TiN_xO_y is exposed on
the surface of the stent.
5. (Original) The stent of Claim 4, wherein x is 1 and y is 1 or 2.
6. (Original) The stent of Claim 4, wherein the layer of TiN_xO_y compound is not more than
about 48,000 Å in thickness.
7. (Withdrawn) The stent of Claim 1, wherein the stent is made from stainless steel.
8. (Withdrawn) The stent of Claim 1, wherein the surface is the tissue-contacting surface of
the stent.

9. (Withdrawn) A stent comprising a layer of TiN_xC_y on a surface of the stent and a subsurface compound including Ti, N, or TiN disposed beneath the layer of TiN_xC_y , wherein the subsurface compound is intermixed with a surface material of the stent.
10. (Withdrawn) The stent of Claim 9, wherein a region of the layer of TiN_xC_y is implanted at a depth within a surface of the stent.
11. – 12. (Canceled)
13. (Withdrawn and currently amended) A method of modifying a surface of a stent, comprising implanting a compound including Ti, N, C, ~~or including Ti, N, O, or both~~, on a molecular or atomic level at a depth within a surface of the stent, followed by depositing TiN_xC_y over the implanted compound.
14. (Withdrawn) The method of Claim 13, wherein x is 1 and y is 1 or 2.
15. – 16. (Canceled)
17. (Withdrawn) The method of Claim 13, wherein the stent is made from stainless steel.
18. (Withdrawn and currently amended) The method of Claim 13, wherein prior to the act of implanting the compound including Ti, N, C, ~~or including Ti, N, O, or both~~, within the surface of the stent, the method comprises implanting Ti, N or TiN within the surface of the stent.

19. (Previously presented) A method of modifying a stent surface, comprising implanting Ti or N into the surface of the stent on a molecular or atomic level, followed by implanting TiN over the Ti or N, and followed by forming a layer of a TiN_xO_y compound over at least some of the areas where TiN has been implanted.
20. (Canceled)
21. (Currently Amended) A stent comprising: a first region having Ti or N implanted on a molecular or atomic level at a depth ~~with~~within at least a region of a surface of the stent~~[[,]]~~; a second region over the first region having TiN implanted on a molecular or atomic level at a depth ~~with~~within at least a region of a surface of the stent; and a layer of TiN_xO_y compound over the second region.
22. – 23. (Canceled)
24. (Previously Presented) The stent of Claim 21, wherein the stent is made from stainless steel.
25. (Previously Presented) The stent of Claim 21, wherein the surface is the tissue-contacting surface of the stent.
26. (Withdrawn) A stent comprising a layer of TiN_xC_y exposed on the surface of the stent, the stent having a surface material different than TiN_xC_y and a compound including Ti, N, or TiN, disposed beneath the layer of TiN_xC_y such that the compound is blended with the surface material of the stent.
27. (Withdrawn) The stent of Claim 26, wherein a region of the layer of TiN_xC_y is implanted at a depth within a surface of the stent.

28. – 33. (Canceled)

34. (Withdrawn) A stent comprising a TiN_xC_y compound implanted on a molecular or atomic level at a depth within at least a region of a surface of the stent.

35. – 41. (Canceled)

42. (Withdrawn) The stent of Claim 34, additionally comprising a layer of a TiN_xC_y compound on the region of the surface of the stent wherein the TiN_xC_y compound is implanted.

43. (Withdrawn) A method of modifying a stent surface, comprising implanting on a molecular or atomic level Ti, N, or TiN into the surface of the stent and forming a layer of a TiN_xC_y compound over the areas where Ti, N, or TiN has been implanted.

44. (Withdrawn) A method of modifying a surface of a stent, comprising implanting a TiN_xC_y compound on a molecular or atomic level at a depth within a surface of the stent or depositing the compound on the surface of the stent.

45. (Withdrawn) The stent of Claim 1, wherein the layer of TiN_xC_y is exposed on a surface of the stent.